II. LISTING OF THE CLAIMS

The following listing of claims replaces all prior versions, and listings, of claims in the application:

1. (Currently amended) A method for polishing a wafer, the method comprising the steps of:

providing a semiconductor wafer having a topography including a first topography location and a different second topography location;

applying a slurry that includes an additive for forming a polishing inhibiting layer in situ across the topography, wherein the additive and a surface of the topography have opposite electrostatic charges to ensure adhesion of the polishing inhibiting layer to the surface of the topography, the polishing inhibiting layer creating a polishing rate for the topography that is non-linear with polishing pressure; wherein the additive includes one of: an anionic surfactant and a cationic surfactant and wherein the cationic surfactant includes a chemical structure selected from the group consisting of:

a) $[CH_3(CH_2)_xN(R)]M$, wherein M is selected from the group consisting of: Cl, Br and I, x equals an integer between 2 and 24, and the R includes three carbon-based functional groups, each having less than eight carbon atoms; and

b) C_pH_qQN, where Q is selected from the group consisting of: Cl, Br and I, and $p > 8$ and $q > 20$;

and;

chemical mechanical polishing the topography.

2. (Canceled).

3. (Canceled).

4. (Currently Amended) The method of claim [[3]] 1, wherein the carbon-based functional groups are selected from the group consisting of: CH_3, CH_2OH, C_2H_4OH, C_2H_5, C_3H_6OH and C_3H_7.

5. (Currently Amended) The method of claim [[2]] 1, wherein the cationic surfactant includes C_pH_qQN, and Q is Cl, p = 21, and q = 38, resulting in cetylpyridinium chloride ($C_{21}H_{38}ClN$).

6. (Currently Amended) The method of claim [[2]] 1, wherein the cationic surfactant includes one of: cetyltrimethyl ammonium bromide (CTAB), $[CH_3(CH_2)_{15}N(CH_3)_3]Br$; cetyldimethylethyl ammonium bromide (CDB), $[CH_3(CH_2)_{15}N(CH_3)_2CH_2OH]Br$; $[CH_3(CH_2)_xN(CH_3)_3]Br$, where x equals an integer between 2 and 24; and $[CH_3(CH_2)_xN(CH_3)(C_2H_5)(C_3H_7)]Br$, where x equals an integer between 2 and 24.

7. (Currently Amended) The method of claim [[2]] 1, wherein the anionic surfactant includes at least one of: sodium sulfate, sodium dodecyl sulfate, sodium lauryl sulfate, sodium stearate and sodium tetradecyl sulfate.

8. (Original) The method of claim 1, wherein the polishing inhibiting layer decreases a polishing rate of one of the topography locations to a level defined according to: $PR = k * (P - P_{crit})$,

where PR is the polishing rate, k is a coefficient of friction of a slurry, P is a polishing pad polishing pressure at one of the topography locations, and P_{crit} is a critical removal polishing pressure to be applied for removal of the polishing inhibiting layer.

9. (Original) The method of claim 8, further comprising the step of removing the polishing inhibiting layer by polishing at a pressure greater than the critical removal polishing pressure.

10. (Original) The method of claim 8, wherein the critical removal polishing pressure P_{crit} is no less than approximately 2 psi and no greater than approximately 20 psi.

11. (Original) The method of claim 8, wherein the polishing step includes applying a downforce of no more than 4 psi above the critical removal polishing pressure P_{crit}, and no less than 4 psi below the critical removing polishing pressure P_{crit}.

12. (Previously Presented) The method of claim 1, further comprising the step of controlling a pH level of the slurry to be between an isoelectric point of the topography and an isoelectric point of a polishing particle of the slurry to ensure adhesion of the polishing inhibiting layer to the surface of the topography, wherein the controlling step includes adding at least one of an acid

and a base.

13. (Original) The method of claim 12, wherein the acid is selected from the group consisting of: nitric acid, hydrochloric acid, phosphoric acid and sulfuric acid, and the base selected from the group consisting of: potassium hydroxide and sodium hydroxide.

14. (Original) The method of claim 1, wherein the difference in topography between the first topography location and the second topography location is at least one of: height and pattern density.

15. (Original) The method of claim 1, wherein the topography includes silicon dioxide, the slurry includes a polishing particle including ceria, the additive includes cetyltrimethyl ammonium bromide (CTAB) $[CH_3(CH_2)_{15}N(CH_3)_3]Br$, and a pH level of the slurry is no less than approximately 2 and no more than approximately 7.

16. (Original) The method of claim 1, wherein the topography includes silicon nitride, the slurry includes a polishing particle including silica, the additive includes sodium dodecylsulfate, and a pH level of the slurry is no less than approximately 3 and no more than approximately 9.

17-30. (Canceled).